### **Description**

The HI6908 uses advanced trench technology

to provide excellent  $R_{DS(ON)}$ , This device is suitable

for use as a load switch or in PWM applications.

#### **General Features**

 $V_{DS} = 60V, I_{D} = 5A$ 

 $R_{DS(ON)}$  < 49m $\Omega$  @  $V_{GS}$ = 10V

## **Application**

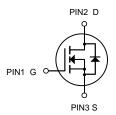
Battery protection

Load switch

Uninterruptible power supply



SOT-23



N-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
HI6908	SOT-23	6005	3000

### Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	60	V
Vgs	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous	5	А
Ірм	Drain Current-Pulsed (Note 1)	30	А
P <sub>D</sub>	Maximum Power Dissipation	3	W
Тл,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	°C
Rеja	Thermal Resistance, Junction-to-Ambient (Note 2)	73	°C/W



# **Electrical Characteristics** (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units	
Off Charac	Off Characteristic						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	-	-	V	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V,	-	-	1.0	μA	
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA	
On Charac	On Characteristics						
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1	1.6	2.5	V	
D	Static Drain-Source on-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =5A	-	40	49	mΩ	
R <sub>DS(on)</sub>		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	-	45	63		
Dynamic C	Dynamic Characteristics						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	825	-	pF	
Coss	Output Capacitance		-	49	-	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	41	-	pF	
Qg	Total Gate Charge	V <sub>DS</sub> =30V, I <sub>D</sub> =4.5A,	-	14	-	nC	
Q <sub>gs</sub>	Gate-Source Charge		-	2.9	-	nC	
Q <sub>gd</sub>	Gate-Drain("Miller") Charge	V <sub>GS</sub> =10V	-	5.2	-	nC	
Switching	Switching Characteristics						
t <sub>d(on)</sub>	Turn-on Delay Time		-	5	-	ns	
t <sub>r</sub>	Turn-on Rise Time	V <sub>DS</sub> =30V,I <sub>D</sub> =2A,	-	2.6	-	ns	
t <sub>d(off)</sub>	Turn-off Delay Time	$R_L=6.7\Omega, R_G=3\Omega,$	-	16.1	-	ns	
t <sub>f</sub>	Turn-off Fall Time	V <sub>GS</sub> =10V	-	2.3	-	ns	
Drain-Soul	rce Diode Characteristics and Maxim	um Ratings					
	Maximum Continuous Drain to Source	Diode Forward			E	Λ	
Is	Current		-	-	5	Α	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	30	Α	
V <sub>SD</sub>	Drain to Source Diode Forward	V <sub>GS</sub> =0V, I <sub>S</sub> =15A	_	_	1.2	V	
VSD	Voltage	VGS-UV, IS-13A		_	1.2	V	
trr	Body Diode Reverse Recovery Time	   Tյ=25℃,I <sub>F</sub> =15A,	-	35	-	ns	
Qrr	Body Diode Reverse Recovery	dl/dt=100A/µs	_	53	_	nC	
G(I)	Charge	a a.c. 1007 11 po				110	

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

<sup>2.</sup> EAS condition : TJ=25  $^{\circ}\text{C}$  ,VDD=30V,VG=10V,L=0.5mH,Rg=25 $\Omega$ ,IAS=6.1A

<sup>3.</sup> Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



# **Typical Performance Characteristics**

Figure1: Output Characteristics

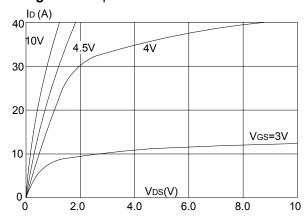


Figure 3:On-resistance vs. Drain Current

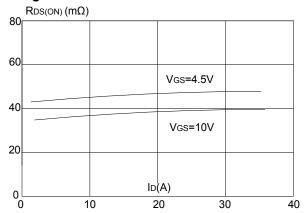


Figure 5: Gate Charge Characteristics

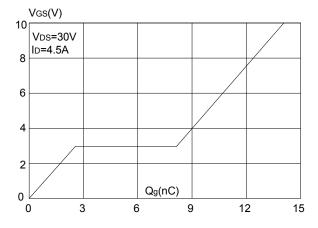


Figure 2: Typical Transfer Characteristics

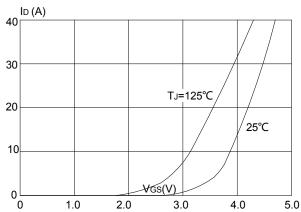


Figure 4: Body Diode Characteristics

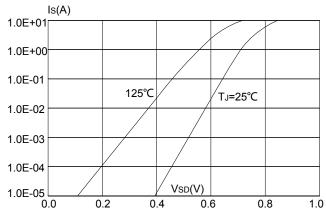
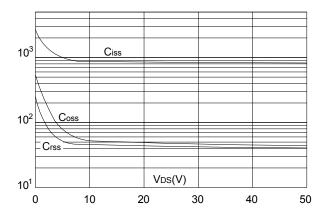


Figure 6: Capacitance Characteristics





**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

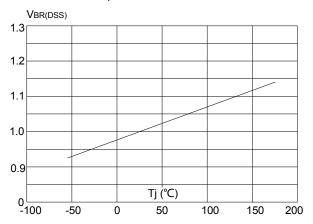
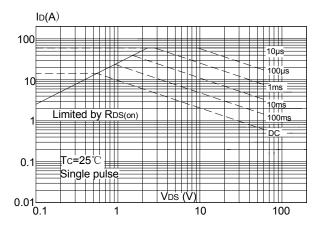
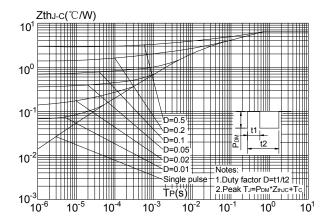
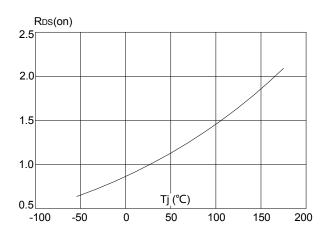


Figure 9: Maximum Safe Operating Area

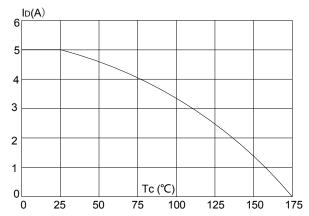


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case



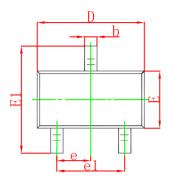


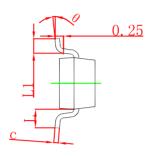
**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

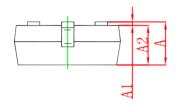




## **SOT-23 Package Outline Dimensions**

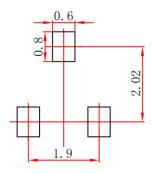






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Зупроі	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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